

L Number	Hits	Search Text	DB	Time stamp
1	778	257/329	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/18 14:31
2	1127	257/330	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/18 14:47
3	585	257/331	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/18 14:55

L Number	Hits	Search Text	DB	Time stamp
1	4465	(257/57, 59, 66, 72, 347, "350").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/18 15:26

L Number	Hits	Search Text	DB	Time stamp
1	20524	semiconductor and (tft or (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/18 15:01
2	1755	(semiconductor and (tft or (thin adj film adj transistor))) and gate and source and drain and offset	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/18 15:03
3	258	((semiconductor and (tft or (thin adj film adj transistor))) and gate and source and drain and offset) and sidewall	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/18 15:03
4	191	((((semiconductor and (tft or (thin adj film adj transistor))) and gate and source and drain and offset) and sidewall) and (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/18 15:04
5	66	(((((semiconductor and (tft or (thin adj film adj transistor))) and gate and source and drain and offset) and sidewall) and (gate adj electrode)) and (offset adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/18 15:04